

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	233	438/132.ccls.	USPAT	OR	OFF	2004/12/04 13:24
L2	218	438/600.ccls.	USPAT	OR	OFF	2004/12/04 13:24
L3	238	438/601.ccls.	USPAT	OR	OFF	2004/12/04 13:24
L4	543	257/529.ccls.	USPAT	OR	OFF	2004/12/04 13:26
L5	442	257/328.ccls.	USPAT	OR	OFF	2004/12/04 13:28
L6	537	kim-hyun\$.in.	USPAT	OR	OFF	2004/12/04 13:26
L7	436	kim-hyun\$.in.	US-PGPUB	OR	OFF	2004/12/04 13:26
L8	528	kim-hyun\$.in.	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/04 13:26
L9	6276	fuse and conduct\$6 and (insulat\$6 dielectric) and pattern\$6	USPAT	OR	OFF	2004/12/04 13:29
L10	6276	9 and (fuse and conduct\$6 and (insulat\$6 dielectric) and pattern\$6)	USPAT	OR	ON	2004/12/04 13:35
L11	6065	10 and (via hole contact plug open\$6 window)	USPAT	OR	ON	2004/12/04 13:31
L12	5576	11 and (metal\$6 wir\$6)	USPAT	OR	ON	2004/12/04 13:32
L13	2110	12 and (pattern\$ same metal\$6)	USPAT	OR	ON	2004/12/04 13:35
L14	1900	13 and (etch\$6 remov\$6)	USPAT	OR	ON	2004/12/04 13:34
L15	1372	14 and (memory DRAM cell electrode)	USPAT	OR	ON	2004/12/04 13:36
L16	2239	(fuse and conduct\$6 and (insulat\$6 dielectric) and pattern\$6)	US-PGPUB	OR	ON	2004/12/04 13:36
L17	858	16 and (pattern\$ same metal\$6)	US-PGPUB	OR	ON	2004/12/04 13:35
L18	702	17 and (memory DRAM cell electrode)	US-PGPUB	OR	ON	2004/12/04 13:36
L19	327	(fuse and conduct\$6 and (insulat\$6 dielectric) and pattern\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/04 13:36